

ABSTRACT OF THE DISCLOSURE

In a wafer treatment apparatus, a hydrofluoric acid gas supply pipe and an evacuation pipe are connected to a chamber storing a wafer for performing prescribed treatment. A control part is provided for controlling supply of hydrofluoric acid gas. The control part sets a time for supplying the hydrofluoric acid gas into the chamber to be longer than a time up to starting of etching of a reaction product and shorter than a time up to starting of etching of a gate insulator film. Thus, only the reaction product can be substantially etched without etching the gate insulator film.